

5V, High-Precision, Ultra-Low-Power Operational Amplifiers

1. FEATURES

Nanopower supply current: 570nA/channel

Offset voltage: 210µV (max)

TcVos: 1.2µV/°C

Unity gain-bandwidth: 11kHz
Wide supply range: 1.6V to 5.5V
Low input bias current: 0.1pA

Unity-gain stable

Rail-to-rail input and output

EMI protection

Shut-down

2. APPLICATIONS

CO and O² gas detectors

PIR motion detectors

Ionization smoke alarms

Thermostats

IoT remote sensors

Active RFID readers and tags

Portable medical equipment

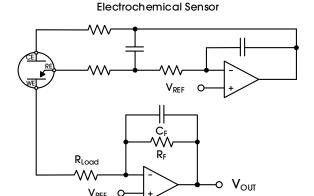
Monitor and alarms

Wearable devices

3. DESCRIPTION

The OPA503/4 is one of the ultra-low-power family operational amplifiers provided by AnalogySemi. With just 570nA of quiescent current and operating voltage ranged between 1.6V and 5.5V, the OPA503/4 operational amplifier is applicable to most battery-powered circumstances and stable even without additional boost topology. Keeping low power consumption and 11kHz of bandwidth, the OPA503/4 device works rather well with equipment such as CO detectors, smoke detectors, and PIR motion detectors. In addition, the OPA503/4 operational amplifier has CMOS input stages with typically femto-amp bias currents. EMI protection is incorporated into the OPA503/4 design in order to enhance overall system reliability by reducing system sensitivity to undesirable RF signals from mobile phones, Wi-Fi, radio transmitters, and tag readers. The EN pin can be used in low power application to save power.

The OPA503/4 operational amplifier is offered in the SOT23-5 and SOT23-6 package respectively. All versions are specified from -40°C to 125°C, which makes them suitable for various rugged environment. See Table 1 for the order information.



Nanopower Amplifier in

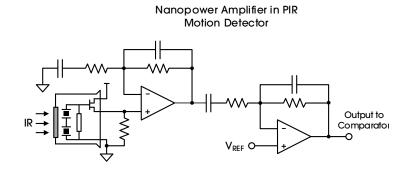


Table 1 lists the order information.

Table 1. Order Information

Order Number ⁽¹⁾	CH(#)	Package	Marking	l₀ per CH (Typ) (nA)	GBW (kHz)	Slew Rate (Typ) (V/ms)	Noise nV/√Hz (100Hz)	Operating Temp (°C)	Package Option
OPA503ASOT235	1	SOT23-5	OPA503	570	11	3	214	-40-125	T/R-3000
OPA504ASOT236	1	SOT23-6	OPA504	570	11	3	214	-40-125	T/R-3000

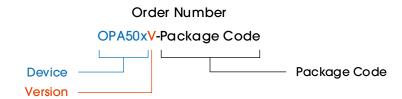
Table 2. Family Selection Guide

Order Number ⁽¹⁾	CH(#)	Package	Marking	l _Q per CH (Typ) (nA)	GBW (kHz)	Slew Rate (Typ) (V/ms)	Noise nV/√Hz (100Hz)	Operating Temp (°C)	Package Option
OPA501BSOT235	1	SOT23-5	OPA501	240	4.2	1.3	347	-40-125	T/R-3000
OPA505ASOT235	1	SOT23-5	OPA505	3200	65	20	100	-40-125	T/R-3000
OPA506ASOT236	1	SOT23-6	OPA506	3200	65	20	100	-40-125	T/R-3000

Devices can be ordered via the following two ways:

- 1. Place orders directly on our website (www.analogysemi.com), or;
- 2. Contact our sales team by mailing to sales@analogysemi.com.

Note:



4. PIN CONFIGURATION AND FUNCTIONS

Figure 1 illustrates the pin configuration.

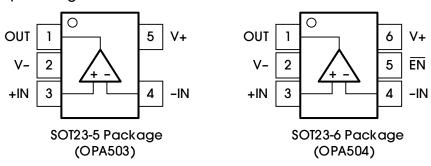


Figure 1. Pin Configuration

Table 3 lists the pin functions.

Table 3. Pin Functions

PO	SITION				
SOT23-5 (OPA503)	SOT23-6 (OPA504)	NAME	TYPE	DESCRIPTION	
1	1	OUT	Output	Output	
2	2	V-	Power	Negative (lowest) power supply	
3	3	+IN	Input	Positive (non-inverting) input	
4	4	-IN	Input	Negative (inverting) input	
5	6	V+	Power	Positive (highest) power supply	
_	5	EN	Input	Pull to V- to enable operation	

5. SPECIFICATIONS

5.1 ABSOLUTE MAXIMUM RATINGS

Table 4 lists the absolute maximum ratings of the OPA503/4. Over operating free-air temperature range, unless otherwise noted.

Table 4. Absolute Maximum Ratings

PARAMETER	DES	SCRIPTION	MIN	MAX	UNITS
	Supply		-0.3	6	
Voltage	Signal input pine(2)(3)	Common-mode	(V-) - 0.3	(V+) + 0.3	V
	Signal input pins ⁽²⁾⁽³⁾	Differential	(V-) - 0.3	(V+) + 0.3	
Current	Signal input pins		-10	10	mA
Current	Output short-circuit ⁽⁴⁾		Conti	nuous	
	Operating, T _A		-40	125	
Temperature	Junction, T _J		150	°C	
	Storage, T _{stg}	-65	150	1	

- Note 1: Stresses beyond those listed under Table 4 may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Table 6. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- Note 2: Not to exceed -0.3V or +6.0V on ANY pin, referred to V-.
- Note 3: Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.3V beyond the supply rails should be current-limited to 10mA or less.
- Note 4: Short-circuit to $V_{\rm S}$ / 2, one amplifier per package. Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C.

5.2 ESD RATINGS

Table 5 lists the ESD ratings of the OPA503/4.

Table 5. ESD Ratinas

PARAMETER	SYMBOL	DESCRIPTION	VALUE	UNITS
Electrostatic	V _(ESD)	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±6000	٧
Discharge	▼ (E2D)	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±2000	·

- Note 1: The JEDEC document JEP155 indicates that 500V HBM allows safe manufacturing with a standard ESD control process.
- Note 2: The JEDEC document JEP157 indicates that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 RECOMMENDED OPERATING CONDITIONS

Table 6 lists the recommended operating conditions for the OPA503/4. Over operating free-air temperature range, unless otherwise noted.

Table 6. Recommended Operating Conditions

PARAMETER	MIN	NOM	MAX	UNITS
Operating Voltage Range	1.6		5.5	٧
Specified Temperature Range	-40		125	°C

5.4 THERMAL INFORMATION

Table 7 lists the thermal information for the OPA503/4.

Table 7. Thermal Information

PARAMETER	SYMBOL	SOT23-5	SOT23-6	UNITS
Junction-to-Ambient Thermal Resistance	$R_{\Theta JA}$	168	169	°C/W
Junction-to-Case (Top) Thermal Resistance	R ₀ JC(top)	103	109	°C/W
Junction-to-Board Thermal Resistance	$R_{\Theta JB}$	39	28	°C/W
Junction-to-Top Characterization Parameter	τιΨ	10	11	°C/W
Junction-to-Board Characterization Parameter	Ψлв	36	28	°C/W
Junction-to-Case (Bottom) Thermal Resistance	R ₀ JC(bot)	66	59	°C/W

5.5 ELECTRICAL CHARACTERISTICS

Table 8 lists the electrical characteristics of OPA503/4. $T_A = 25^{\circ}C$, $V_S = 1.8V$ to 5V, $V_{CM} = V_{OUT} = V_S$ / 2, and $R_L \ge 10M\Omega$ to V_S / 2, unless otherwise noted.

Table 8. Electrical Characteristics

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
OFFSET VOLTAGE	1					
Input Offset Voltage	Vos	$V_S = 1.8V, 3.3V, \text{ and 5V}, V_{CM} = V_S/2 \text{ or } V_{CM} = (V+) - 0.9V$		±52	±210	μV
Input Offset Drift	$\Delta V_{OS}/\Delta T$	$V_{CM} = V_{-}, T_{A} = -40^{\circ}C \text{ to } 125^{\circ}C$		1.2		μV/°C
Power-Supply Rejection Ratio	PSRR	$V_{S} = 1.8V$ to 5V, $V_{CM} = VDD/2$		15	93	μV/V
INPUT VOLTAGE RANGE						
Common-Mode Voltage Range	V _{CM}		0		VDD	V
Common-Mode Rejection Ratio	CMRR	$(V-) \le V_{CM} \le (V+), V_S = 5V$	77	94		dB
INPUT BIAS CURRENT						
Input Bias Current	I _B	$V_S = 1.8V$, $V_{CM} = V_S / 2$		±100		fA
Input Offset Current	los	$V_S = 1.8V$, $V_{CM} = V_S / 2$		±100		
INPUT IMPEDANCE	T			1	1	
Differential ⁽¹⁾				3.3		рF
Common Mode ⁽¹⁾				7.2		
NOISE		14			1	
Input Voltage Noise	En	f = 0.1Hz to 10Hz		9.1		μV_{pp}
Input Voltage Noise Density	en	f = 100Hz $f = 1kHz$		214 238		nV/√Hz
OPEN-LOOP GAIN						
Open-Loop Voltage Gain	A _{OL}	$(V-) + 0.3V \le V_O \le (V+) - 0.3V$, $R_L = 100k\Omega$		120		dB
OUTPUT						
Voltage Output Swing from Positive Rail	V _{OH}	$V_S = 1.8V$, $R_L = 100k\Omega$ to (V+) / 2		2	10	m)/
Voltage Output Swing from Negative Rail	V _{OL}	$V_S = 1.8V$, $R_L = 100k\Omega$ to (V+)/2		1.5	10	mV
Short-Circuit Current	I _{SC}	$V_S = 3.3V$, short to $V_S / 2$		10		mA
FREQUENCY RESPONSE						
Gain-Bandwidth Product	GBP	$C_L = 20pF$, $R_L = 10M\Omega$, $V_S = 5V$		11		kHz
Slew Rate (10% to	SR	G = 1, Rising Edge, $C_L = 20pF$, $V_S = 5V$		3		V/ms
90%)		G = 1, Falling Edge, $C_L = 20pF$, $V_S = 5V$		6		V/1115
POWER SUPPLY						
Quiescent Current		$V_{CM} = V_{-}, I_{O} = 0, V_{S} = 3.3V$		570	705	nA
Shutdown Current		$V_{CM} = V_{-}, I_{O} = 0, V_{S} = 3.3V, \overline{EN} = VDD,$ OPA504		40	100	nA
LOGIC INPUT						
Enable Input High	V _{IH}		V+	V+		V
Enable Input Low	V_{IL}			V-	V-	V

Note: Guaranteed by design.

5.6 TYPICAL CHARACTERISTICS

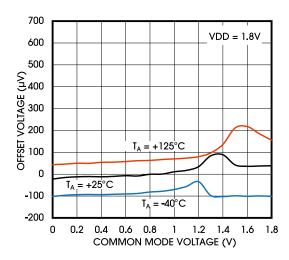


Figure 2. Typical Offset Voltage vs. Common Mode Voltage, 1.8V

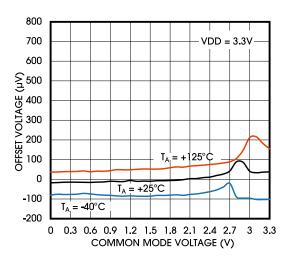


Figure 4. Typical Offset Voltage vs. Common Mode Voltage, 3.3V

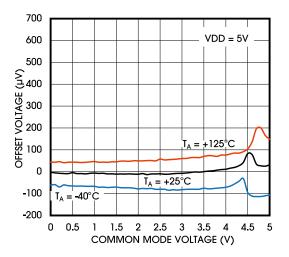


Figure 6. Typical Offset Voltage vs. Common Mode Voltage, 5V

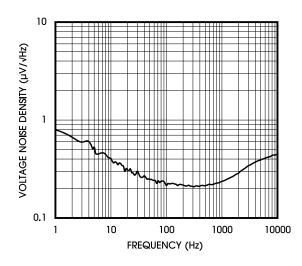


Figure 3. Input Voltage Noise vs. Frequency

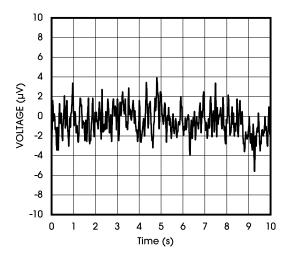


Figure 5. Integrated Noise

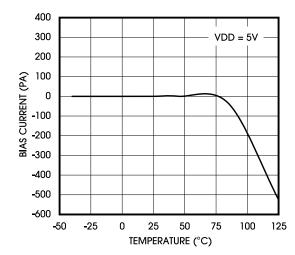
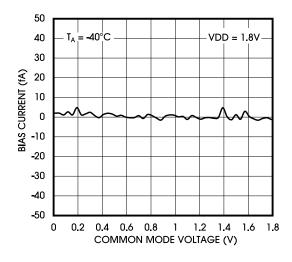


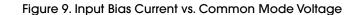
Figure 7. Input Bias Current vs. Temperature

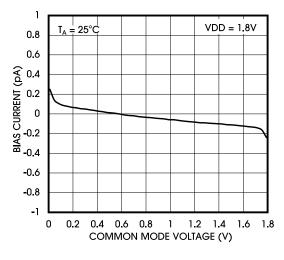
5.7 TYPICAL CHARACTERISTICS (CONTINUED)



1 0.8 0.6 (VDD = 5V — VDD = 5V —

Figure 8. Input Bias Current vs. Common Mode Voltage





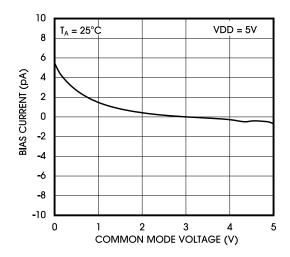
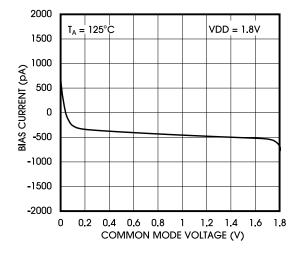


Figure 10. Input Bias Current vs. Common Mode Voltage

Figure 11. Input Bias Current vs. Common Mode Voltage



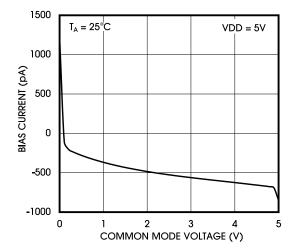


Figure 12. Input Bias Current vs. Common Mode Voltage

Figure 13. Input Bias Current vs. Common Mode Voltage

5.8 TYPICAL CHARACTERISTICS (CONTINUED)

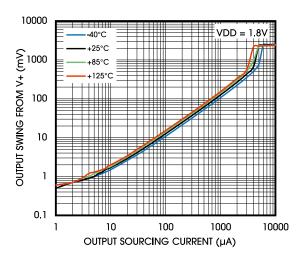


Figure 14. Output Swing vs. Sourcing Current, 1.8V

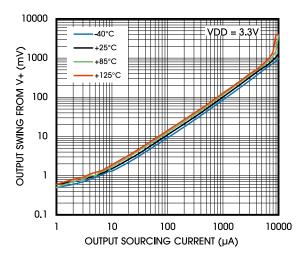


Figure 16. Output Swing vs. Sourcing Current, 3.3V

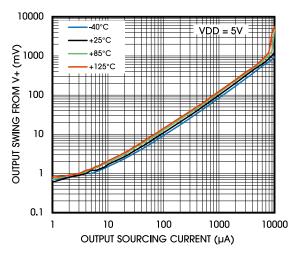


Figure 18. Output Swing vs. Sourcing Current, 5V

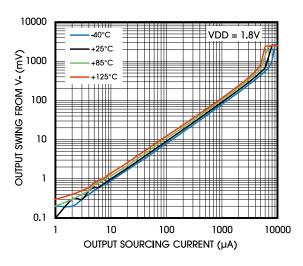


Figure 15. Output Swing vs. Sinking Current, 1.8V

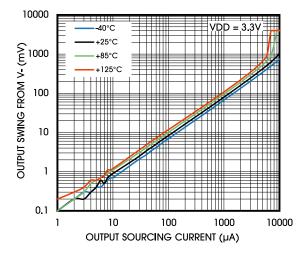


Figure 17. Output Swing vs. Sinking Current, 3.3V

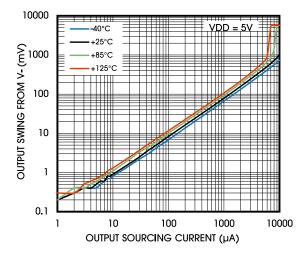


Figure 19. Output Swing vs. Sinking Current, 5V

5.9 TYPICAL CHARACTERISTICS (CONTINUED)

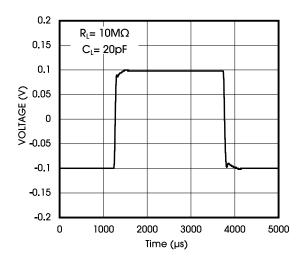


Figure 20. Small Signal Pulse Response, 1.8V

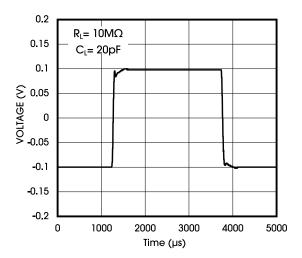


Figure 22. Small Signal Pulse Response, 3.3V

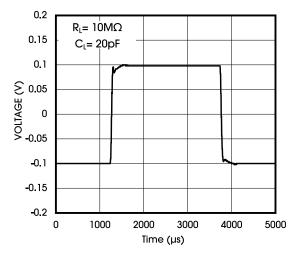


Figure 24. Small Signal Pulse Response, 5V

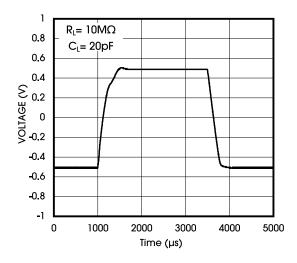


Figure 21. Large Signal Pulse Response, 1.8V

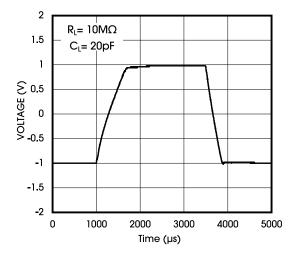


Figure 23. Large Signal Pulse Response, 3.3V

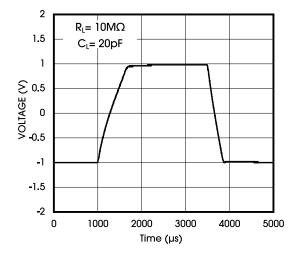
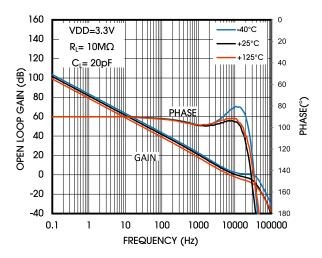


Figure 25. Large Signal Pulse Response, 5V

5.10 TYPICAL CHARACTERISTICS (CONTINUED)



140 120 100 100 80 80 40 20 0 1 10 100 1000 10000 FREQUENCY (Hz)

Figure 26. Open Loop Gain and Phase, 3.3V, $10M\Omega$ Load

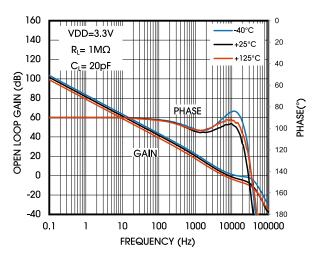


Figure 27. CMRR vs. Frequency

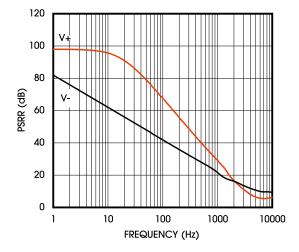


Figure 28. Open Loop Gain and Phase, 3.3V, $1 M\Omega$ Load

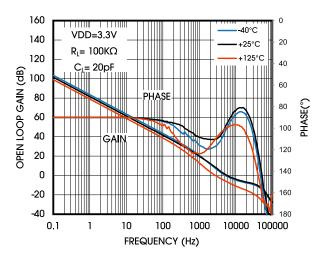


Figure 29. PSRR vs. Frequency

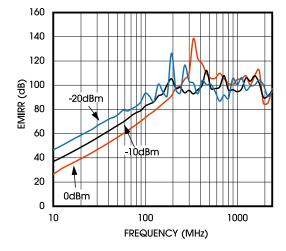


Figure 30. Open Loop Gain and Phase, 3.3V, $100 \text{k}\Omega$ Load

Figure 31. EMIRR Performance

5.11 TYPICAL CHARACTERISTICS (CONTINUED)

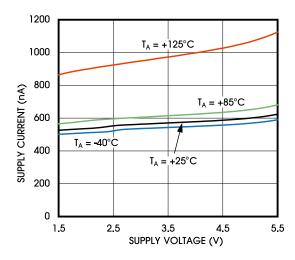


Figure 32. Supply Current vs. Supply Voltage

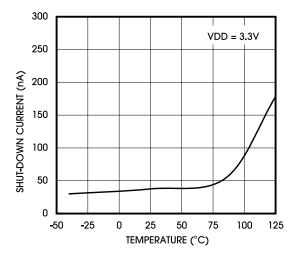


Figure 33. Shut-Down Current vs. Temperature

6. DETRILED DESCRIPTION

6.1 OVERVIEW

The OPA503/4 nanopower CMOS operational amplifier is designed for long-life battery-powered and energy harvested applications. They can operate on a single supply with operation as low as 1.6V. Low input bias current make it an ideal choice for sensor interface, in particular for sensors that operate with low voltage and at low frequency. The common-mode range extends to the power supply, making it ideal for single-supply applications. EMI protection has been employed internally to reduce the effects of EMI.

6.2 FEATURE DESCRIPTION

6.2.1 RAIL-TO-RAIL INPUT

The OPA503/4 features a rail-to-rail input with 100fA bias current, making it ideal for sensor like CO and O² gas detectors. Low input bias current contributes less error to sensor. See Figure 7 through Figure 13 for typical input bias current.

6.2.2 RAIL-TO-RAIL OUTPUT STAG€

The OPA503/4 output voltage swings 2mV from rails at 1.8V supply, which provides the maximum possible dynamic range at the output. This is particularly important when operating on low supply voltages. The Maximum Output Voltage Swing graph defines the maximum swing possible under a particular output load. See Figure 14 through Figure 19.

6.2.3 POWER SUPPLY

Connect a 100nF capacitor as close as possible to the V+/V- pin, to reduce ripple of power supply. Care need be taken while selecting the capacitor, as the OPA503/4 is nanopower component, in low power application, static leakage current of ceramic capacitor cannot be ignored, especially at high temperature. Usually high-voltage ceramic capacitor has low static leakage current, use a high-voltage ceramic capacitor or film capacitor when static leakage current matters.

When designing for ultralow power, choose system feedback components carefully. To minimize quiescent current consumption, select large-value feedback resistors. Any large resistors will react with stray capacitance in the circuit and the input capacitance of the operational amplifier. These parasitic RC combinations can affect the stability of the overall system. A feedback capacitor may be required to assure stability and limit overshoot or gain peaking. When possible, use AC coupling and AC feedback to reduce static current draw through the feedback elements. Use film or ceramic capacitors since large electrolytic may have large static leakage currents in the nanoamps.

6.2.4 SHUTDOWN OP€RATION

The device features an active-low enable mode, pulling the \overline{EN} pin to V- for normal operation. To shut down the device, pull the \overline{EN} pin to V+. In shutdown mode, the quiescent current is only 40nA, significantly reducing power consumption.

It is highly recommended to connect the \overline{EN} pin to V+ or V- to enable high (V_{II}) or low (V_{IL}) threshold voltages. Putting the \overline{EN} pin in the middle of V+ and V- may cause high-supply current.

6.2.5 DRIVING CAPACITIVE LOAD

The OPA503/4 is internally compensated for stable unity gain operation, with a 4.2kHz typical gain bandwidth. However, the unity gain follower is the most sensitive configuration to capacitive load. The combination of a capacitive load placed directly on the output of an amplifier along with the amplifier's output impedance creates a phase lag, which reduces the phase margin of the amplifier. If the phase margin is significantly reduced, the response will be under damped, which causes peaking in the transfer and, when there is too much peaking, the op amp might start oscillating.

In order to drive heavy (> 50pF) capacitive loads, an isolation resistor, $R_{\rm ISO}$, should be used. By using this isolation resistor, the capacitive load is isolated from the amplifier's output. The larger the value of $R_{\rm ISO}$, the more stable the amplifier will be. If the value of $R_{\rm ISO}$ is sufficiently large, the feedback loop will be stable, independent of the value of C_L . However, larger values of $R_{\rm ISO}$ result in reduced output swing and reduced output current drive. The recommended value for $R_{\rm ISO}$ is 30-50k Ω .

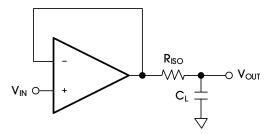


Figure 34. Resistive Isolation of Capacitive Load

6.2.6 PCB LAYOUT RECOMMENDATION

Take care about layout routing. Parasitic capacitor on the input and output can significantly lower phase margin and bandwidth. For some applications like unit gain, if there is ground shield in inner layer or bottom layer, fine routing is recommended, or use bottom layer instead of inner layer as ground shield. Furthermore, the routing of input and output should be as short as possible.

7. PACKAGE INFORMATION

7.1 SOT23-5 PACKAGE

Figure 35 shows the SOT23-5 package view.

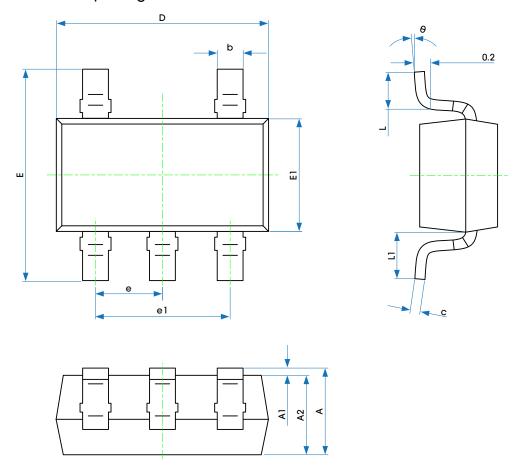


Figure 35. SOT23-5 Package View

Table 9 provides detailed information about the dimensions of the SOT23-5 package.

Table 9. Dimensions of the SOT23-5 Package

SYMBOL	DIMENSIONS I	n millimeters	DIMENSIONS	S IN INCHES
STIVIBOL	MIN	MAX	MIN	MAX
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	2.650	2.950	0.104	0.116
E1	1.500	1.700	0.059	0.067
е	0.950	(BSC)	0.037 ((BSC)
el	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
L1	0.600	REF.	0.024	REF.
θ	0°	8°	0°	8°

7.2 SOT23-6 PACKAGE

Figure 36 shows the SOT23-6 package view.

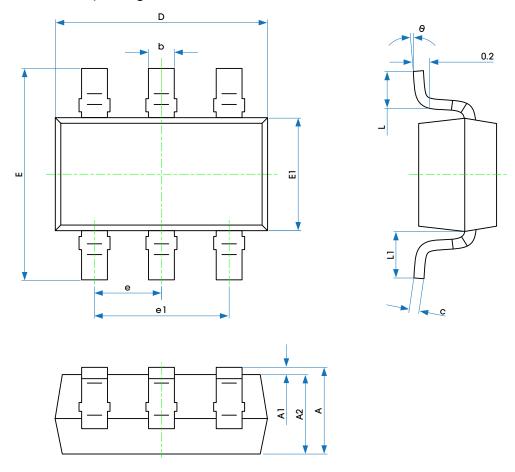


Figure 36. SOT23-6 Package View

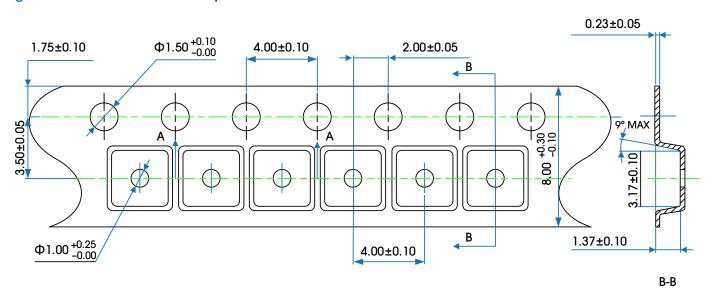
Table 10 provides detailed information about the dimensions of the SOT23-6 package.

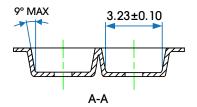
Table 10. Dimensions of the SOT23-6 Package

SYMBOL	DIMENSIONS	IN MILLIMETERS	DIMENSIONS	IN INCHES
STIVIBOL	MIN	MAX	MIN	MAX
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	2.650	2.950	0.104	0.116
El	1.500	1.700	0.059	0.067
е	0.950	(BSC)	0.037 (BSC)
el	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
L1	0.60	0 REF.	0.024	REF.
θ	0°	8°	0°	8°

8. TAPE AND REEL INFORMATION

Figure 37 illustrates the carrier tape.





Notes:

- 1. Cover tape width: 5.50 ± 0.10 .
- 2. Cumulative tolerance of 10 sprocket hole pitch: ±0.20 (max).
- 3. Camber: not to exceed 2mm in 250mm.
- 4. Mold#: SOT23-5/SOT23-6.
- 5. All dimensions: mm.
- 6. Direction of view:

Figure 37. Carrier Tape Drawing

Table 11 provides information about tape and reel.

Table 11. Tape and Reel Information

PACKAGE TYPE	REEL	QTY/REEL	REEL/ INNER BOX	INNER BOX/ CARTON	QTY/CARTON	INNER BOX SIZE (MM)	CARTON SIZE (MM)
SOT23-5 (OPA503)/ SOT23-6 (OPA504)	7''	3000	10	4	120000	210*208*203	440*440*230

Figure 38 shows the product loading orientation—pin 1 is assigned on the lower left corner.

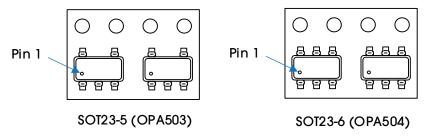


Figure 38. Product Loading Orientation

REVISION HISTORY

REVISION	DATE	DESCRIPTION
Rev A	30 March 2022	Rev A release.
Rev B	31 March 2022	Updated the PACKAGE OPTION columns in Table 1 and Table 2.

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